

# FSFR2100 — Fairchild Power Switch (FPS™) for Half-Bridge Resonant Converters

## Features

- Variable Frequency Control with 50% Duty Cycle for Half-bridge Resonant Converter Topology
- High Efficiency through Zero Voltage Switching (ZVS)
- Internal SuperFET™s with Fast-Recovery Type Body Diode ( $t_{rr}=120$  ns)
- Fixed Dead Time (350 ns) Optimized for MOSFETs
- Up to 300kHz Operating Frequency
- Pulse Skipping for Frequency Limit (Programmable) at Light-Load Condition
- Remote On/Off Control Using Control Pin
- Protection Functions: Over-Voltage Protection (OVP), Over-Load Protection (OLP), Over-Current Protection (OCP), Abnormal Over-Current Protection (AOCP), Internal Thermal Shutdown (TSD)

## Applications

- PDP and LCD TVs
- Desktop PCs and Servers
- Adapters
- Telecom Power Supplies
- Audio Power Supplies

## Description

The FSFR2100 is a highly integrated power switch designed for high-efficiency half-bridge resonant converters. Offering everything necessary to build a reliable and robust resonant converter, the FSFR2100 simplifies designs and improves productivity, while improving performance. The FSFR2100 combines power MOSFETs with fast-recovery type body diodes, a high-side gate-drive circuit, an accurate current controlled oscillator, frequency limit circuit, soft-start, and built-in protection functions. The high-side gate-drive circuit has a common-mode noise cancellation capability, which guarantees stable operation with excellent noise immunity. The fast-recovery body diode of the MOSFETs improves reliability against abnormal operation conditions, while minimizing the effect of the reverse recovery. Using the zero-voltage-switching (ZVS) technique dramatically reduces the switching losses and efficiency is significantly improved. The ZVS also reduces the switching noise noticeably, which allows a small-sized Electromagnetic Interference (EMI) filter.

The FSFR2100 can be applied to various resonant converter topologies, such as: series resonant, parallel resonant, and LLC resonant converters.

## Related Resources

- [AN-4151 — Half-Bridge LLC Resonant Converter Design Using FSFR2100 Fairchild Power Switch \(FPS™\)](#)
- [Evaluation Board: FEBFSFR2100\\_D015v1](#)

## Ordering Information

| Part Number | Package | Operating Junction Temperature | $R_{DS(ON\_MAX)}$ | Maximum Output Power without Heatsink ( $V_{IN}=350\sim400$ V) <sup>(1,2)</sup> | Maximum Output Power with Heatsink ( $V_{IN}=350\sim400$ V) <sup>(1,2)</sup> |
|-------------|---------|--------------------------------|-------------------|---|--|
| FSFR2100    | 9-SIP   | -40 to +130°C                  | 0.38 $\Omega$     | 200 W   | 450 W  |

### Notes:

1. The junction temperature can limit the maximum output power.
2. Maximum practical continuous power in an open-frame design at 50°C ambient.

### Application Circuit Diagram

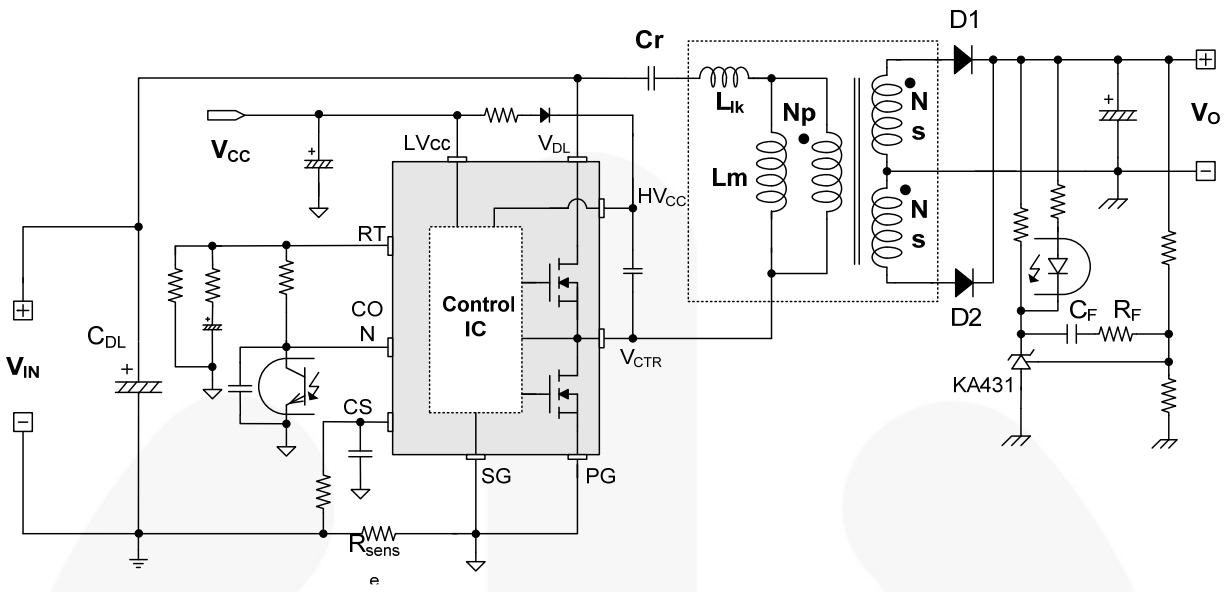


Figure 1. Typical Application Circuit (LLC Resonant Half-Bridge Converter)

### Block Diagram

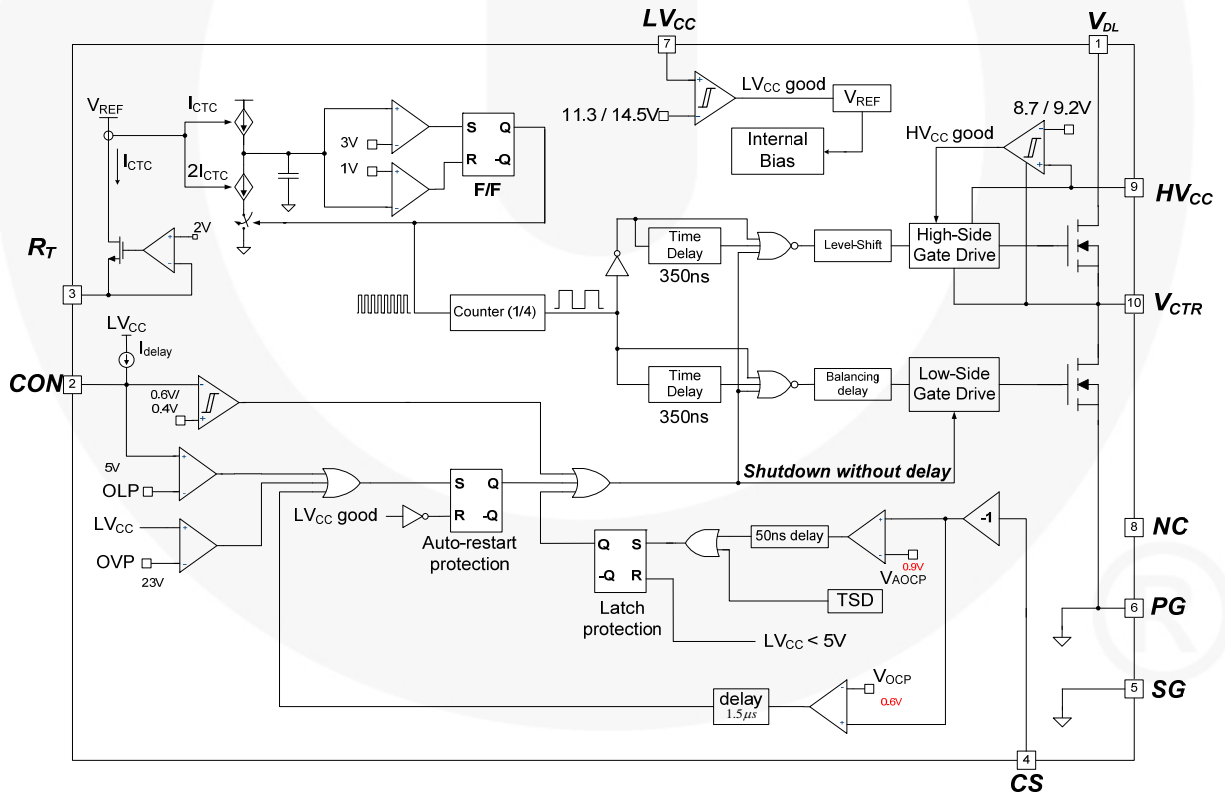


Figure 2. Internal Block Diagram

## Pin Configuration

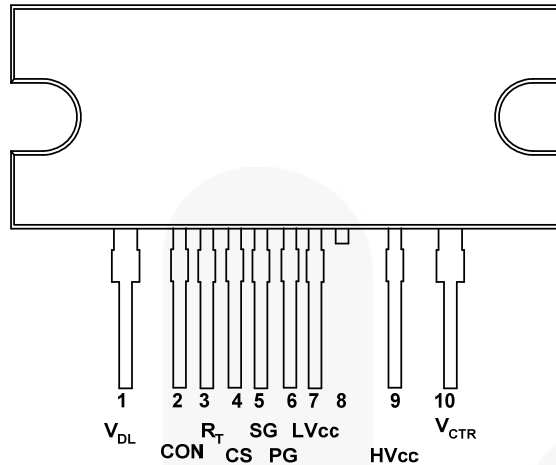


Figure 3. Package Diagram

## Pin Definitions

| Pin # | Name             | Description   |
|-------|------------------|---|
| 1     | V <sub>DL</sub>  | This is the drain of the high-side MOSFET, typically connected to the input DC link voltage.  |
| 2     | CON              | This pin is for enable/disable and protection. When the voltage of this pin is above 0.6 V, the IC operation is enabled. When the voltage of this pin drops below 0.4 V, gate drive signals for both MOSFETs are disabled. When the voltage of this pin increases above 5 V, protection is triggered. |
| 3     | R <sub>T</sub>   | This pin programs the switching frequency. Typically, an opto-coupler is connected to control the switching frequency for the output voltage regulation.  |
| 4     | CS               | This pin senses the current flowing through the low-side MOSFET. Typically, negative voltage is applied on this pin.  |
| 5     | SG               | This pin is the control ground.   |
| 6     | PG               | This pin is the power ground. This pin is connected to the source of the low-side MOSFET.   |
| 7     | LV <sub>CC</sub> | This pin is the supply voltage of the control IC.   |
| 8     | NC               | No connection.  |
| 9     | HV <sub>CC</sub> | This is the supply voltage of the high-side gate-drive circuit IC.  |
| 10    | V <sub>CTR</sub> | This is the drain of the low-side MOSFET. Typically, a transformer is connected to this pin.  |

## Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.  $T_A=25^{\circ}\text{C}$  unless otherwise specified.

| Symbol                 | Parameter   | Min.                      | Max.      | Unit   |
|------------------------|---|---------------------------|-----------|--------|
| $V_{DS}$               | Maximum Drain-to-Source Voltage ( $V_{DL}-V_{CTR}$ and $V_{CTR}-PG$ ) | 600                       |           | V      |
| $LV_{CC}$              | Low-Side Supply Voltage   | -0.3                      | 25.0      | V      |
| $HV_{CC}$ to $V_{CTR}$ | High-Side $V_{CC}$ Pin to Low-side Drain Voltage                      | -0.3                      | 25.0      | V      |
| $HV_{CC}$              | High-Side Floating Supply Voltage                                     | -0.3                      | 625.0     | V      |
| $V_{CON}$              | Control Pin Input Voltage   | -0.3                      | $LV_{CC}$ | V      |
| $V_{CS}$               | Current Sense (CS) Pin Input Voltage                                  | -5.0                      | 1.0       | V      |
| $V_{RT}$               | $R_T$ Pin Input Voltage   | -0.3                      | 5.0       | V      |
| $dV_{CTR}/dt$          | Allowable Low-Side MOSFET Drain Voltage Slew Rate                     |                           | 50        | V/ns   |
| $P_D$                  | Total Power Dissipation <sup>(3)</sup>                                |                           | 12        | W      |
| $T_J$                  | Maximum Junction Temperature <sup>(4)</sup>                           |                           | +150      | °C     |
|                        | Recommended Operating Junction Temperature <sup>(4)</sup>             | -40                       | +130      |        |
| $T_{STG}$              | Storage Temperature Range   | -55                       | +150      | °C     |
| <b>MOSFET Section</b>  |   |                           |           |        |
| $V_{DGR}$              | Drain Gate Voltage ( $R_{GS}=1\text{ M}\Omega$ )                      | 600                       |           | V      |
| $V_{GS}$               | Gate Source (GND) Voltage   |                           | $\pm 30$  | V      |
| $I_{DM}$               | Drain Current Pulsed <sup>(5)</sup>                                   |                           | 33        | A      |
| $I_D$                  | Continuous Drain Current  | $T_C=25^{\circ}\text{C}$  | 11        | A      |
|                        |   | $T_C=100^{\circ}\text{C}$ | 7         |        |
| <b>Package Section</b> |   |                           |           |        |
| Torque                 | Recommended Screw Torque  |                           | 5~7       | kgf·cm |

### Notes:

- Per MOSFET when both MOSFETs are conducting.
- The maximum value of the recommended operating junction temperature is limited by thermal shutdown.
- Pulse width is limited by maximum junction temperature.

## Thermal Impedance

$T_A=25^{\circ}\text{C}$  unless otherwise specified.

| Symbol        | Parameter   | Value | Unit |
|---------------|---|-------|------|
| $\theta_{JC}$ | Junction-to-Case Center Thermal Impedance (Both MOSFETs Conducting) | 10.44 | °C/W |
| $\theta_{JA}$ | Junction-to-Ambient Thermal Impedance                               | 80    | °C/W |

## Electrical Characteristics

T<sub>A</sub>=25°C unless otherwise specified.

| Symbol                                   | Parameter   | Test Conditions  | Min.  | Typ. | Max. | Unit |
|--|---|--|---|------|------|------|
| <b>MOSFET Section</b>                    |   |  |   |      |      |      |
| BV <sub>DSS</sub>                        | Drain-to-Source Breakdown Voltage   | I <sub>D</sub> =200 μA, T <sub>A</sub> =25°C             | 600   |      |      | V    |
|  |   | I <sub>D</sub> =200 μA, T <sub>A</sub> =125°C            |   | 650  |      |      |
| R <sub>DS(ON)</sub>                      | On-State Resistance   | V <sub>GS</sub> =10 V, I <sub>D</sub> =5.5 A             |   | 0.32 | 0.38 | Ω    |
| t <sub>rr</sub>                          | Body Diode Reverse Recovery Time <sup>(6)</sup>   | V <sub>GS</sub> =0 V, I <sub>Diode</sub> =11.0 A         |   | 120  |      | ns   |
| C <sub>ISS</sub>                         | Input Capacitance <sup>(6)</sup>  | V <sub>DS</sub> =25V, V <sub>GS</sub> =0 V,<br>f=1.0 MHz |   | 1148 |      | pF   |
| C <sub>OSS</sub>                         | Output Capacitance <sup>(6)</sup>   |  |   | 671  |      | pF   |
| <b>Supply Section</b>                    |   |  |   |      |      |      |
| I <sub>LK</sub>                          | Offset Supply Leakage Current   | H-V <sub>CC</sub> =V <sub>CTR</sub> =600 V/500 V         |   |      | 50   | μA   |
| I <sub>QHVCC</sub>                       | Quiescent HV <sub>CC</sub> Supply Current   | (HV <sub>CC</sub> UV+) - 0.1 V                           |   | 50   | 120  | μA   |
| I <sub>QLVCC</sub>                       | Quiescent LV <sub>CC</sub> Supply Current   | (LV <sub>CC</sub> UV+) - 0.1 V                           |   | 100  | 200  | μA   |
| I <sub>OHVCC</sub>                       | Operating HV <sub>CC</sub> Supply Current (RMS Value)                                   | f <sub>OSC</sub> =100 KHz, V <sub>CON</sub> > 0.6 V      |   | 6    | 9    | mA   |
|  |   | No Switching, V <sub>CON</sub> < 0.4 V                   |   | 100  | 200  | μA   |
| I <sub>OLVCC</sub>                       | Operating LV <sub>CC</sub> Supply Current (RMS Value)                                   | f <sub>OSC</sub> =100KHz, V <sub>CON</sub> > 0.6 V       |   | 7    | 11   | mA   |
|  |   | No Switching, V <sub>CON</sub> < 0.4 V                   |   | 2    | 4    | mA   |
| <b>UVLO Section</b>                      |   |  |   |      |      |      |
| LV <sub>CC</sub> UV+                     | LV <sub>CC</sub> Supply Under-Voltage Positive-Going Threshold (LV <sub>CC</sub> Start) |  | 13.0  | 14.5 | 16.0 | V    |
| LV <sub>CC</sub> UV-                     | LV <sub>CC</sub> Supply Under-Voltage Negative-Going Threshold (LV <sub>CC</sub> Stop)  |  | 10.2  | 11.3 | 12.4 | V    |
| LV <sub>CC</sub> UVH                     | LV <sub>CC</sub> Supply Under-Voltage Hysteresis  |  |   | 3.2  |      | V    |
| HV <sub>CC</sub> UV+                     | HV <sub>CC</sub> Supply Under-Voltage Positive-Going Threshold (HV <sub>CC</sub> Start) |  | 8.2   | 9.2  | 10.2 | V    |
| HV <sub>CC</sub> UV-                     | HV <sub>CC</sub> Supply Under-Voltage Negative-Going Threshold (HV <sub>CC</sub> Stop)  |  | 7.8   | 8.7  | 9.6  | V    |
| HV <sub>CC</sub> UVH                     | HV <sub>CC</sub> Supply Under-Voltage Hysteresis  |  |   | 0.5  |      | V    |
| <b>Oscillator &amp; Feedback Section</b> |   |  |   |      |      |      |
| V <sub>CONDIS</sub>                      | Control Pin Disable Threshold Voltage   |  | 0.36  | 0.40 | 0.44 | V    |
| V <sub>CONEN</sub>                       | Control Pin Enable Threshold Voltage  |  | 0.54  | 0.60 | 0.66 | V    |
| V <sub>RT</sub>                          | V-I Converter Threshold Voltage   |  | 1.5   | 2.0  | 2.5  | V    |
| f <sub>OSC</sub>                         | Output Oscillation Frequency  | R <sub>T</sub> =5.2 KΩ                                   | 94  | 100  | 106  | KHz  |
| DC                                       | Output Duty Cycle   |  | 48  | 50   | 52   | %    |
| f <sub>SS</sub>                          | Internal Soft-Start Initial Frequency   |  | f <sub>SS</sub> =f <sub>OSC</sub> +40 kHz, R <sub>T</sub> =5.2 KΩ |      | 140  |      |
| t <sub>SS</sub>                          | Internal Soft-Start Time  |  | 2   | 3    | 4    | ms   |

Continued on the following page...

**Electrical Characteristics** (Continued)

 $T_A=25^{\circ}\text{C}$  unless otherwise specified.

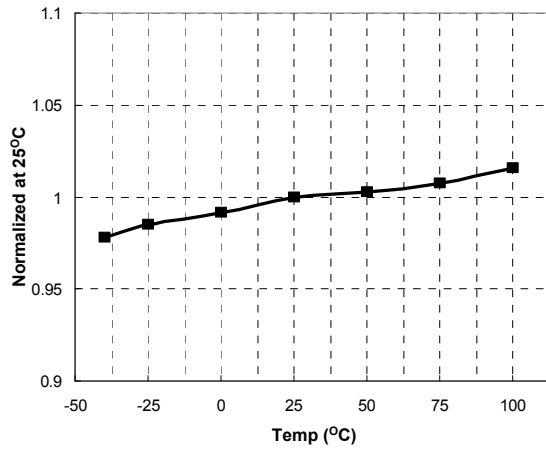
| Symbol                           | Parameter   | Test Conditions   | Min.  | Typ.  | Max.  | Unit               |
|----------------------------------|---|---|-------|-------|-------|--------------------|
| <b>Protection Section</b>        |   |   |       |       |       |                    |
| $I_{OLP}$                        | OLP Delay Current   | $V_{CON}=4\text{ V}$  | 3.6   | 4.8   | 6.0   | $\mu\text{A}$      |
| $V_{OLP}$                        | OLP Protection Voltage  | $V_{CON} > 3.5\text{ V}$  | 4.5   | 5.0   | 5.5   | V                  |
| $V_{OVP}$                        | LV <sub>CC</sub> Over-Voltage Protection  | $L-V_{CC} > 21\text{ V}$  | 21    | 23    | 25    | V                  |
| $V_{AOCP}$                       | AOCP Threshold Voltage  | $\Delta V/\Delta t=-0.1\text{ V}/\mu\text{s}$                       | -1.0  | -0.9  | -0.8  | V                  |
| $t_{BAO}$                        | AOCP Blanking Time <sup>(6)</sup>   | $V_{CS} < V_{AOCP}$ ; $\Delta V/\Delta t=-0.1\text{ V}/\mu\text{s}$ |       | 50    |       | ns                 |
| $V_{OCP}$                        | OCP Threshold Voltage   | $V/\Delta t=-1\text{ V}/\mu\text{s}$                                | -0.64 | -0.58 | -0.52 | V                  |
| $t_{BO}$                         | OCP Blanking Time <sup>(6)</sup>  | $V_{CS} < V_{OCP}$ ; $\Delta V/\Delta t=-1\text{ V}/\mu\text{s}$    | 1.0   | 1.5   | 2.0   | $\mu\text{s}$      |
| $t_{DA}$                         | Delay Time (Low Side) Detecting from V <sub>AOCP</sub> to Switch Off <sup>(6)</sup> | $\Delta V/\Delta t=-1\text{ V}/\mu\text{s}$                         |       | 250   | 400   | ns                 |
| $T_{SD}$                         | Thermal Shutdown Temperature <sup>(6)</sup>   |   | 110   | 130   | 150   | $^{\circ}\text{C}$ |
| $I_{SU}$                         | Protection Latch Sustain LV <sub>CC</sub> Supply Current                            | $LV_{CC}=7.5\text{ V}$  |       | 100   | 150   | $\mu\text{A}$      |
| $V_{PRSET}$                      | Protection Latch Reset LV <sub>CC</sub> Supply Voltage                              |   | 5     |       |       | V                  |
| <b>Dead-Time Control Section</b> |   |   |       |       |       |                    |
| $D_T$                            | Dead Time <sup>(7)</sup>  |   |       | 350   |       | ns                 |

**Notes:**

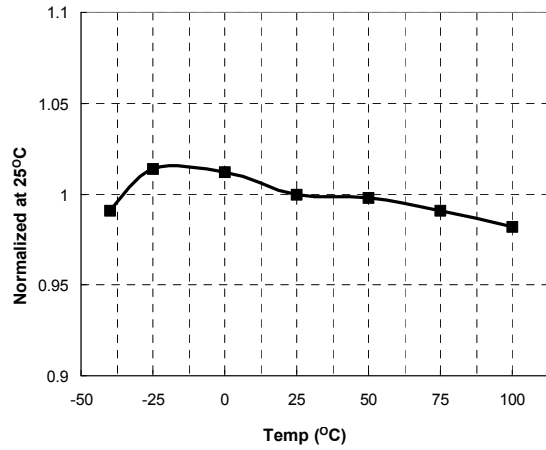
6. This parameter, although guaranteed, is not tested in production.
7. These parameters, although guaranteed, are tested only in EDS (wafer test) process.

## Typical Performance Characteristics

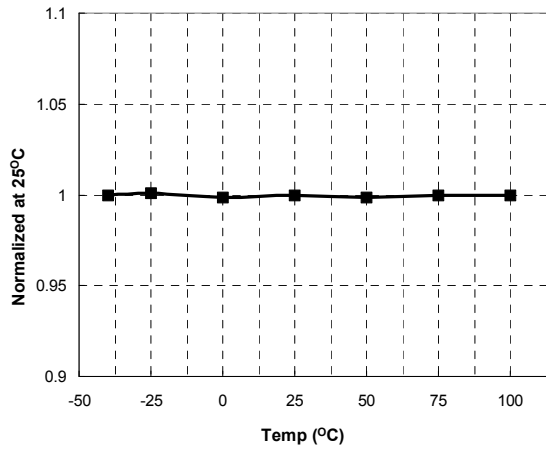
These characteristic graphs are normalized at  $T_A=25^\circ\text{C}$ .



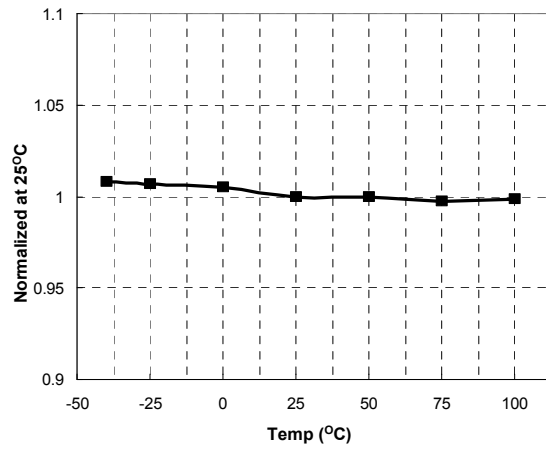
**Figure 4. Low-Side MOSFET Duty Cycle vs. Temperature**



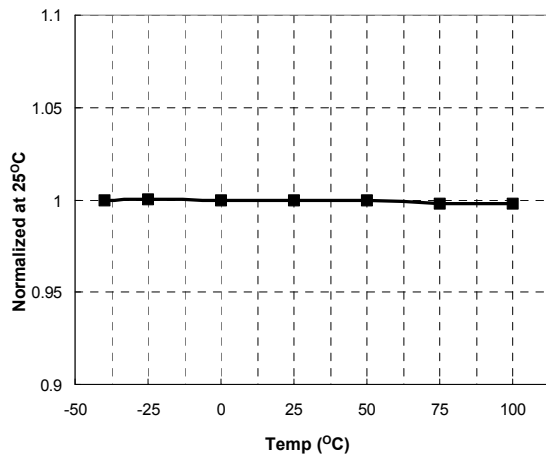
**Figure 5. Switching Frequency vs. Temperature**



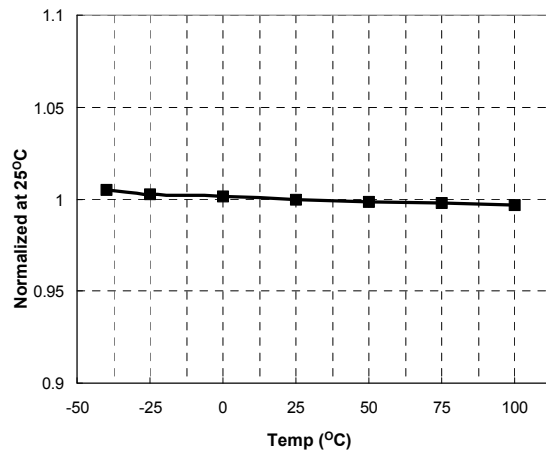
**Figure 6. High-Side  $V_{CC}$  ( $HV_{CC}$ ) Start vs. Temperature**



**Figure 7. High-Side  $V_{CC}$  ( $HV_{CC}$ ) Stop vs. Temperature**



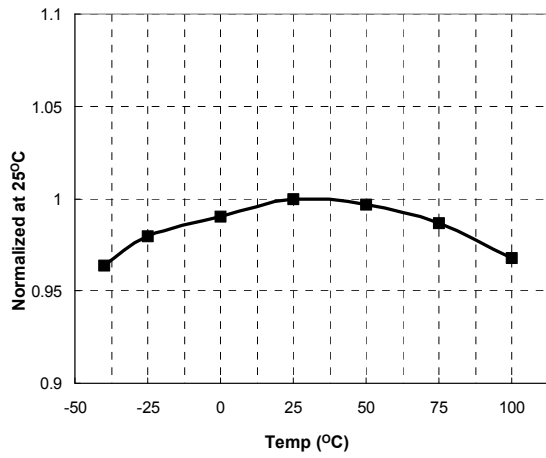
**Figure 8. Low-Side  $V_{CC}$  ( $LV_{CC}$ ) Start vs. Temperature**



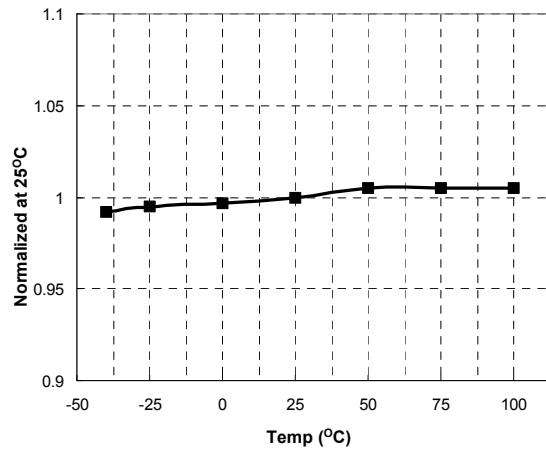
**Figure 9. Low-Side  $V_{CC}$  ( $LV_{CC}$ ) Stop vs. Temperature**

## Typical Performance Characteristics (Continued)

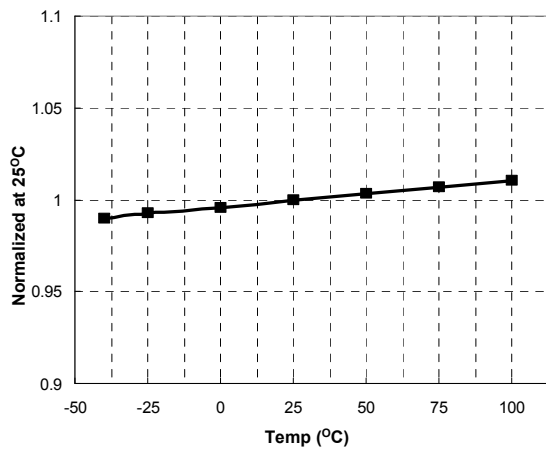
These characteristic graphs are normalized at  $T_A=25^\circ\text{C}$ .



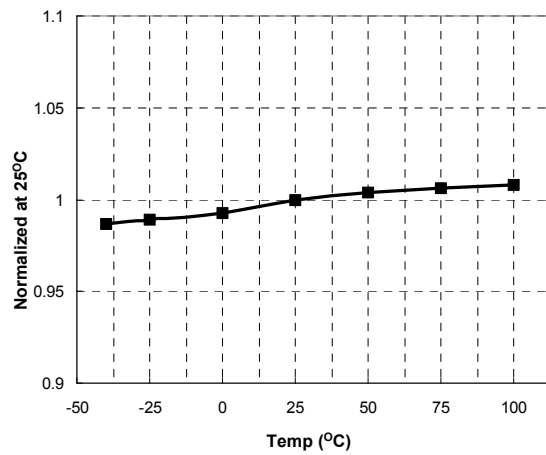
**Figure 10. OLP Delay Current vs. Temperature**



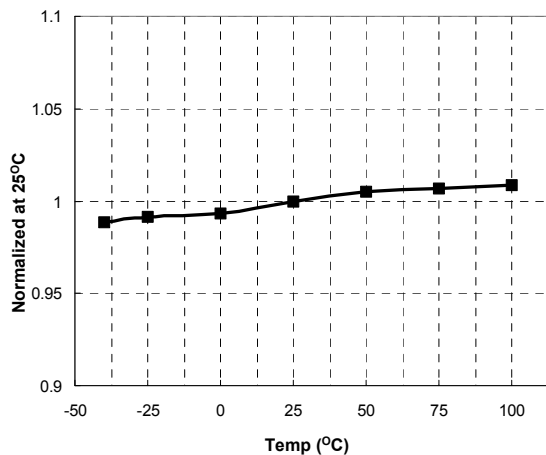
**Figure 11. OLP Protection Voltage vs. Temperature**



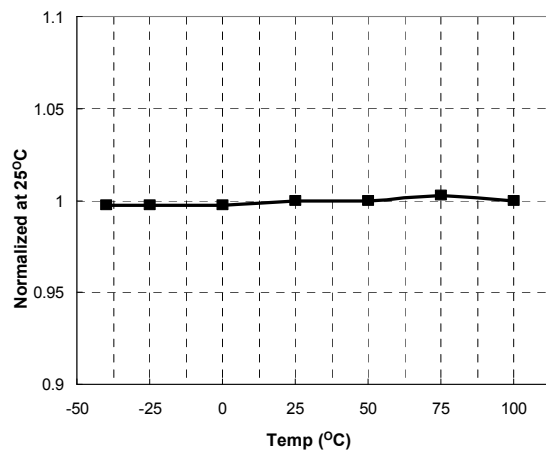
**Figure 12. LV<sub>CC</sub> OVP Voltage vs. Temperature**



**Figure 13. R<sub>T</sub> Voltage vs. Temperature**



**Figure 14. CON Pin Enable Voltage vs. Temperature**



**Figure 15. OCP Voltage vs. Temperature**

## Functional Description

### 1. Basic Operation

FSFR2100 is designed to drive high-side and low-side MOSFETs complementarily with 50% duty cycle. A fixed dead time of 350 ns is introduced between consecutive transitions, as shown in Figure 16.

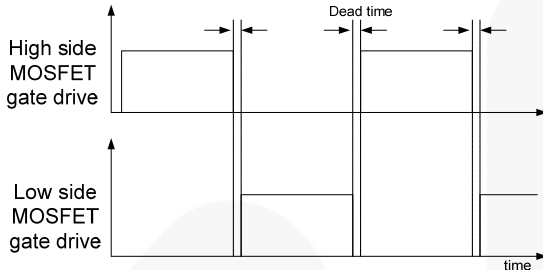


Figure 16. MOSFETs Gate Drive Signal

### 2. Internal Oscillator

FSFR2100 employs a current-controlled oscillator, as shown in Figure 17. Internally, the voltage of  $R_T$  pin is regulated at 2 V and the charging/discharging current for the oscillator capacitor,  $C_T$ , is obtained by copying the current flowing out of  $R_T$  pin ( $I_{CTC}$ ) using a current mirror. Therefore, the switching frequency increases as  $I_{CTC}$  increases.

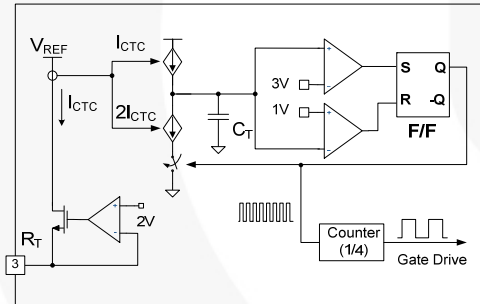


Figure 17. Current Controlled Oscillator

### 3. Frequency Setting

Figure 18 shows a typical voltage gain curve of a resonant converter, where the gain is inversely proportional to the switching frequency in the ZVS region. The output voltage can be regulated by modulating the switching frequency. Figure 19 shows the typical circuit configuration for  $R_T$  pin, where the opto-coupler transistor is connected to the  $R_T$  pin to modulate the switching frequency.

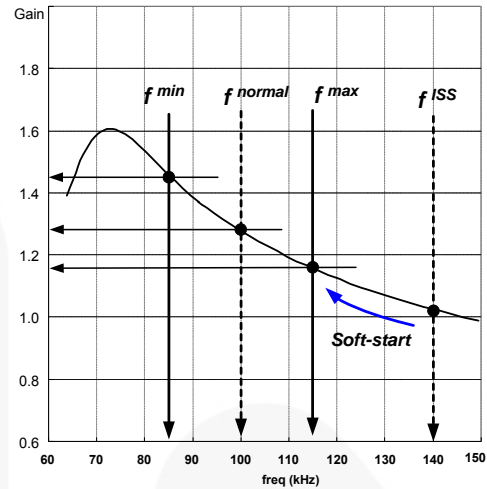


Figure 18. Resonant Converter Typical Gain Curve

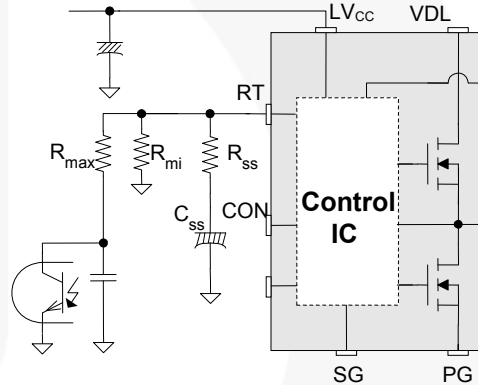


Figure 19. Frequency Control Circuit

The minimum switching frequency is determined as:

$$f^{\min} = \frac{5.2k\Omega}{R_{\min}} \times 100(kHz) \quad (1)$$

Assuming the saturation voltage of opto-coupler transistor is 0.2 V, the maximum switching frequency is determined as:

$$f^{\max} = \left( \frac{5.2k\Omega}{R_{\min}} + \frac{4.68k\Omega}{R_{\max}} \right) \times 100(kHz) \quad (2)$$

To prevent excessive inrush current and overshoot of output voltage during startup, increase the voltage gain of the resonant converter progressively. Since the voltage gain of the resonant converter is inversely proportional to the switching frequency, the soft-start is implemented by sweeping down the switching frequency from an initial high frequency ( $f^{SS}$ ) until the output voltage is established. The soft-start circuit is made by connecting R-C series network on the  $R_T$  pin, as shown in Figure 19. FSFR2100 also has an internal soft-start for

3 ms to reduce the current overshoot during the initial cycles, which adds 40 kHz to the initial frequency of the external soft-start circuit, as shown in Figure 20. The initial frequency of the soft-start is given as:

$$f^{ISS} = \left( \frac{5.2k\Omega}{R_{min}} + \frac{5.2k\Omega}{R_{SS}} \right) \times 100 + 40 \text{ (kHz)} \quad (3)$$

It is typical to set the initial frequency of soft-start two ~ three times the resonant frequency ( $f_0$ ) of the resonant network.

The soft-start time is three to four times of the RC time constant. The RC time constant is as follows:

$$T_{SS} = R_{SS} \cdot C_{SS} \quad (4)$$

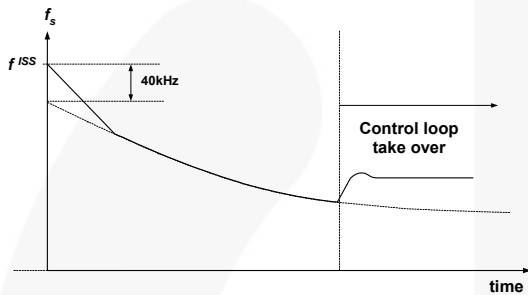


Figure 20. Frequency Sweeping of Soft-start

#### 4. Control Pin

The FSFR2100 has a control pin for protection, cycle skipping, and remote on/off. Figure 21 shows the internal block diagram for control pin.

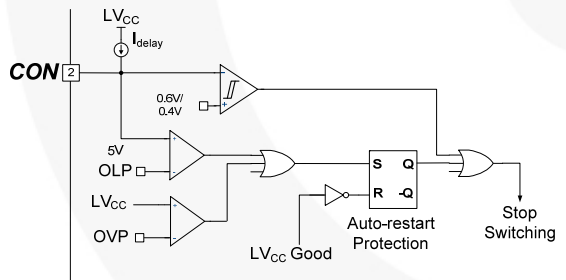


Figure 21. Internal Block of Control Pin

**Protection:** When the control pin voltage exceeds 5V, protection is triggered. Detailed applications are described in the protection section.

**Pulse Skipping:** FSFR2100 stops switching when the control pin voltage drops below 0.4 V and resumes switching when the control pin voltage rises above 0.6 V. To use pulse-skipping, the control pin should be connected to the opto-coupler collector pin. The frequency that causes pulse skipping is given as:

$$f^{SKIP} = \left( \frac{5.2k\Omega}{R_{min}} + \frac{4.16k\Omega}{R_{max}} \right) \times 100 \text{ (kHz)} \quad (5)$$

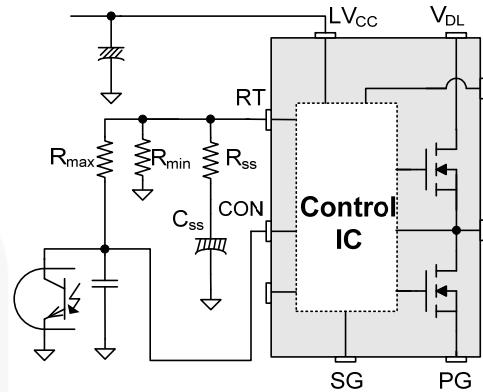


Figure 22. Control Pin Configuration for Pulse Skipping

**Remote On / Off:** When an auxiliary power supply is used for standby, the main power stage using FSFR2100 can be shut down by pulling down the control pin voltage, as shown in Figure 23. R1 and C1 are used to ensure soft-start when switching resumes.

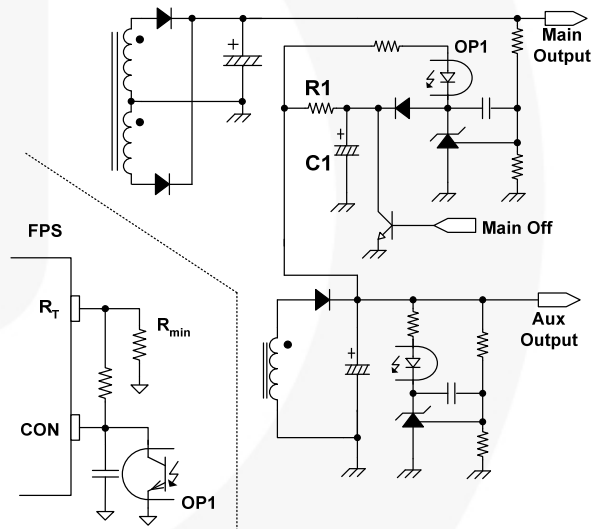


Figure 23. Remote On / Off Circuit

## 5. Current Sensing

**Current Sensing Using Resistor:** FSFR2100 senses drain current as a negative voltage, as shown in Figure 24 and Figure 25. Half-wave sensing allows low power dissipation in the sensing resistor, while full-wave sensing has less switching noise in the sensing signal.

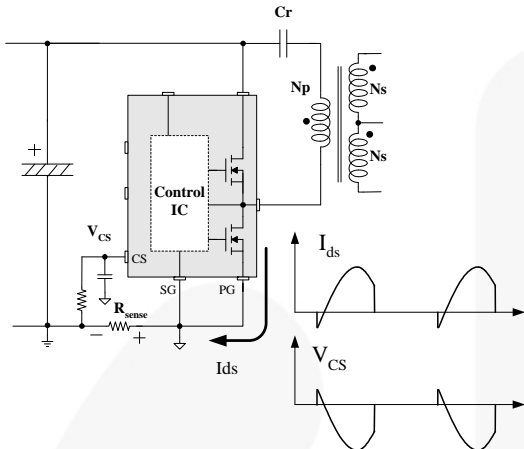


Figure 24. Half-Wave Sensing

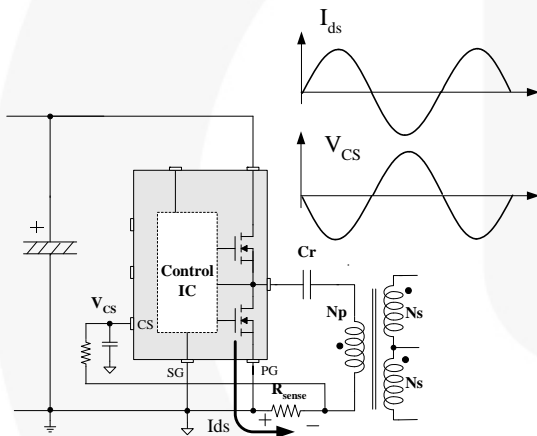


Figure 25. Full-Wave Sensing

### Current Sensing Using Resonant Capacitor Voltage:

For high-power applications, current sensing using a resistor may not be available due to the severe power dissipation in the resistor. In that case, indirect current sensing using the resonant capacitor voltage can be a good alternative because the amplitude of the resonant capacitor voltage ( $V_{Cr}^{p-p}$ ) is proportional to the resonant current in the primary side ( $I_p^{p-p}$ ) as:

$$V_{Cr}^{p-p} = \frac{I_p^{p-p}}{2\pi f_s C_r} \quad (6)$$

To minimize power dissipation, a capacitive voltage divider is generally used for capacitor voltage sensing, as shown in Figure 26.

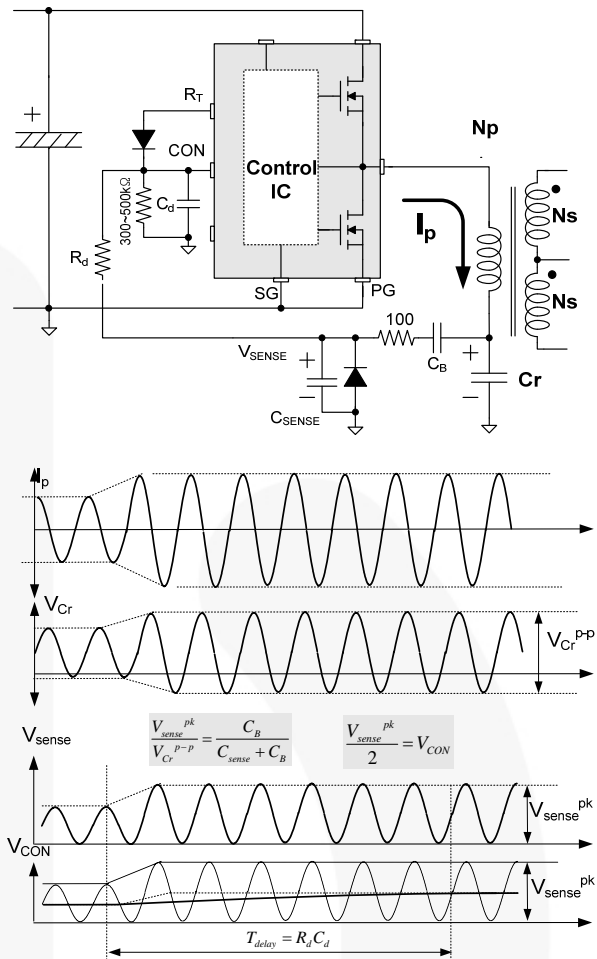


Figure 26. Current Sensing Using Resonant Capacitor Voltage

## 6. Protection Circuits

The FSFR2100 has several self-protective functions, such as Overload Protection (OLP), Over-Current Protection (OCP), Abnormal Over-Current Protection (AOCP), Over-Voltage Protection (OVP), and Thermal Shutdown (TSD). OLP, OCP, and OVP are auto-restart mode protections; while AOCP and TSD are latch-mode protections, as shown in Figure 27.

**6.1 Auto-restart Mode Protection:** Once a fault condition is detected, switching is terminated and the MOSFETs remain off. When  $LV_{CC}$  falls to the  $LV_{CC}$  stop voltage of 11.3 V, the protection is reset. The FPS resumes normal operation when  $LV_{CC}$  reaches the start voltage of 14.5 V.

**6.2 Latch-Mode Protection:** Once this protection is triggered, switching is terminated and the MOSFETs remain off. The latch is reset only when LV<sub>CC</sub> is discharged below 5 V.

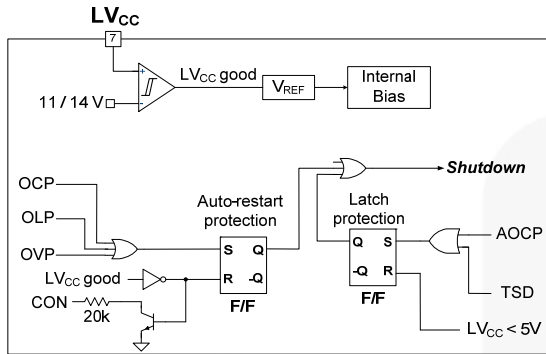


Figure 27. Protection Blocks

**6.3 Over-Current Protection (OCP):** When the sensing pin voltage drops below -0.58 V, OCP is triggered and the MOSFETs remain off. This protection has a shutdown time delay of 1.5 μs to prevent premature shutdown during startup.

**6.4 Abnormal Over-Current Protection (AOCPP):** If the secondary rectifier diodes are shorted, large current with extremely high di/dt can flow through the MOSFET before OCP or OLP is triggered. AOCPP is triggered without shutdown delay when the sensing pin voltage drops below -0.9V. This protection is latch mode and reset when LV<sub>CC</sub> is pulled down below 5 V.

**6.5 Overload Protection (OLP):** Overload is defined as the load current exceeding its normal level due to an unexpected abnormal event. In this situation, the protection circuit should trigger to protect the power supply. However, even when the power supply is in the normal condition, the overload situation can occur during the load transition. To avoid premature triggering of protection, the overload protection circuit should be designed to trigger only after a specified time to determine whether it is a transient situation or a true overload situation. Figure 26 shows a typical overload protection circuit. By sensing the resonant capacitor voltage on the control pin, the overload protection can be implemented. Using RC time constant, shutdown delay can be also introduced. The voltage obtained on the control pin is given as:

$$V_{CON} = \frac{C_B}{2(C_B + C_{sense})} V_{Cr}^{p-p} \quad (7)$$

where  $V_{Cr}^{p-p}$  is the amplitude of the resonant capacitor voltage.

**6.6 Over-Voltage Protection (OVP):** When the LV<sub>CC</sub> reaches 23 V, OVP is triggered. This protection is used when auxiliary winding of the transformer to supply V<sub>CC</sub> to FPS™ is utilized.

**6.7 Thermal Shutdown (TSD):** The MOSFETs and the control IC in one package makes it easy for the control IC to detect the abnormal over-temperature of the MOSFETs. If the temperature exceeds approximately 130°C, the thermal shutdown triggers.

## 7. PCB Layout Guidelines

Duty unbalance problems may occur due to the radiated noise from main transformer, the inequality of the secondary side leakage inductances of main transformer, and so on. Among them, it is one of the dominant reasons that the control components in the vicinity of R<sub>T</sub> pin are enclosed by the primary current flow pattern on PCB layout. The direction of the magnetic field on the components caused by the primary current flow is changed when the high and low side MOSFET turns on by turns. The magnetic fields with opposite direction from each other induce a current through, into, or out of the R<sub>T</sub> pin, which makes the turn-on duration of each MOSFET different. It is highly recommended to separate the control components in the vicinity of R<sub>T</sub> pin from the primary current flow pattern on PCB layout. Figure 28 shows an example for the duty balanced case.

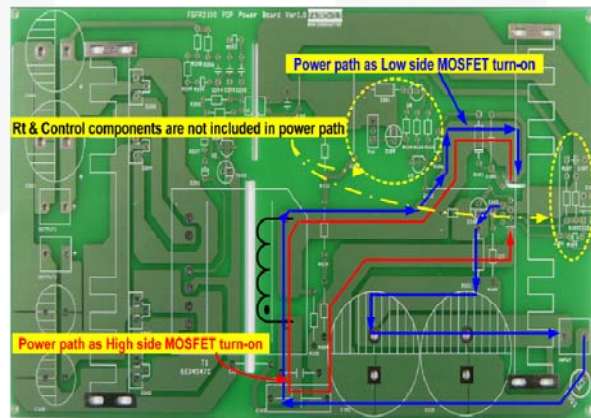


Figure 28. Example for Duty Balancing

## Typical Application Circuit (Half-Bridge LLC Resonant Converter)

| Application | FPS™ Device | Input Voltage Range                               | Rated Output Power | Output Voltage (Rated Current) |
|-------------|-------------|---|--------------------|--------------------------------|
| LCD TV      | FSFR2100    | 390 V <sub>DC</sub><br>(340~400 V <sub>DC</sub> ) | 200 W              | 24 V-8.3 A                     |

### Features

- High efficiency ( >94% at 400 V<sub>DC</sub> input)
- Reduced EMI noise through zero-voltage-switching (ZVS)
- Enhanced system reliability with various protection functions

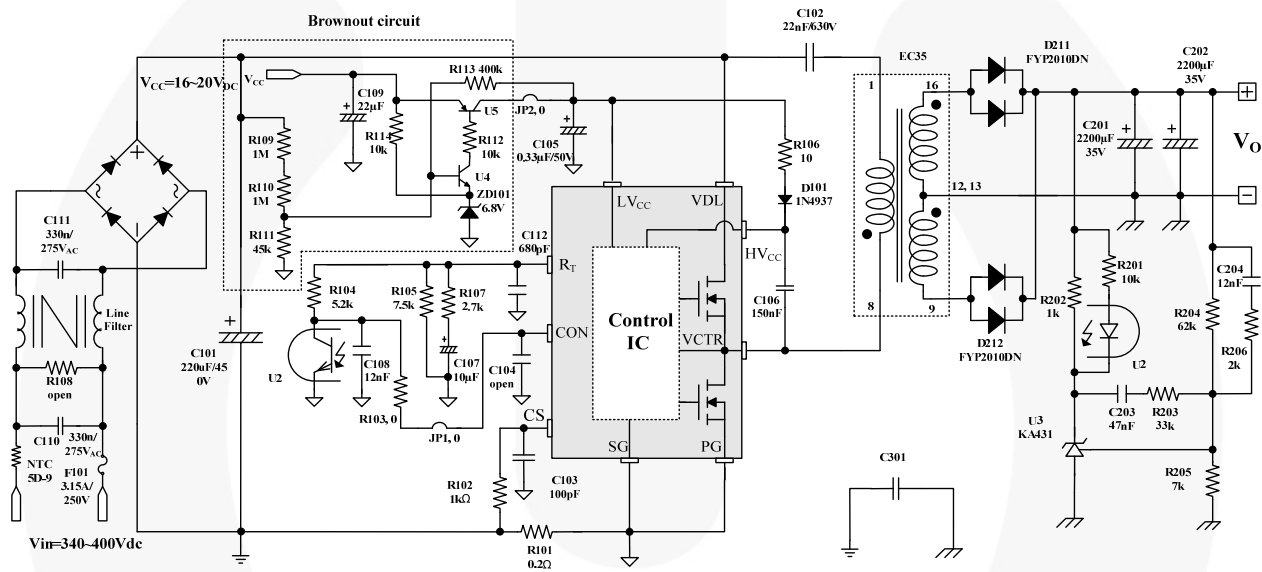


Figure 29. Typical Application Circuit

## Typical Application Circuit (Continued)

Usually, LLC resonant converters require large leakage inductance value. To obtain a large leakage inductance, sectional winding method is used.

- Core: EC35 ( $A_e=106 \text{ mm}^2$ )
- Bobbin: EC35 (Horizontal)
- Transformer Model Number: SNX-2468-1

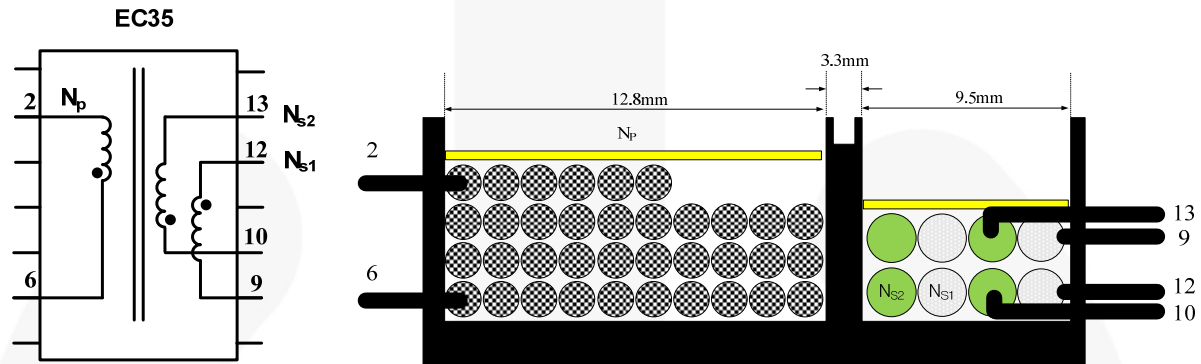


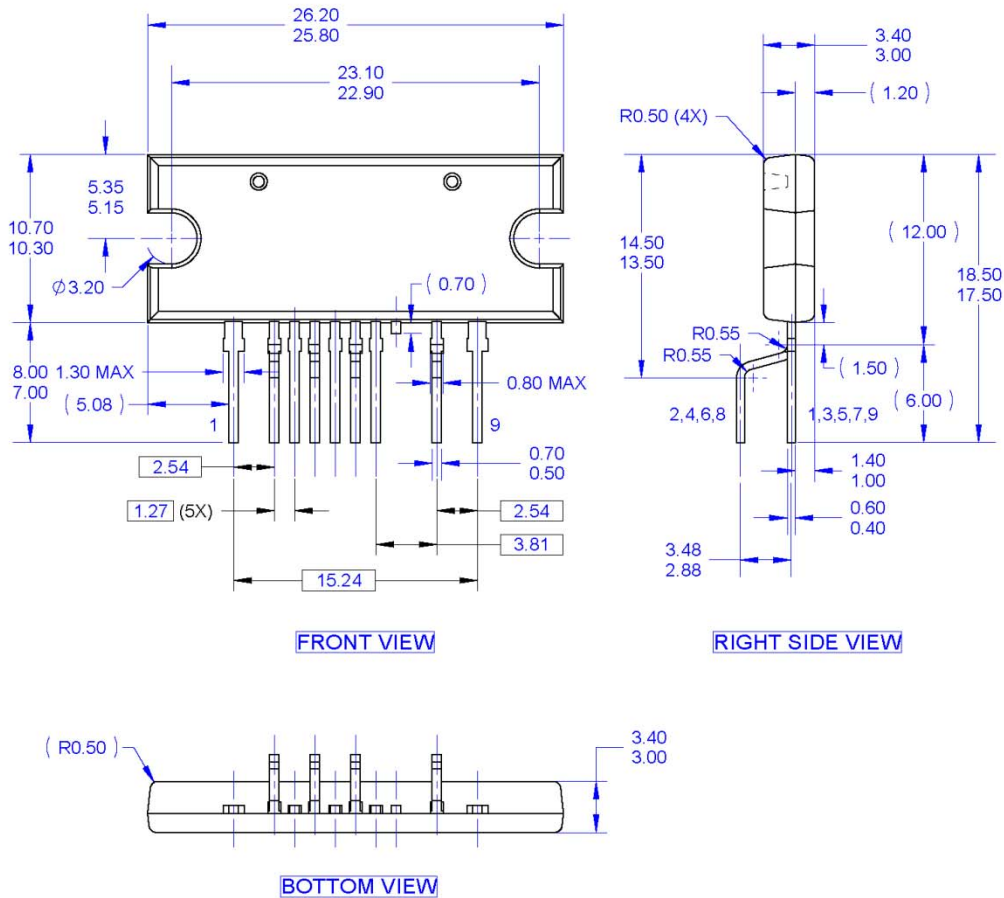
Figure 30. Transformer Construction

|          | Pin (S → F) | Wire                         | Turns | Note            |
|----------|-------------|------------------------------|-------|-----------------|
| $N_p$    | 6 → 2       | 0.08 $\phi$ ×88 (Litz Wire)  | 36    |                 |
| $N_{s1}$ | 12 → 9      | 0.08 $\phi$ ×234 (Litz Wire) | 4     | Bifilar Winding |
| $N_{s2}$ | 10 → 13     | 0.08 $\phi$ ×234 (Litz Wire) | 4     | Bifilar Winding |

|  | Pins | Specifications        | Remark                              |
|--|------|-----------------------|-------------------------------------|
| Primary-Side Inductance ( $L_p$ )        | 2 6  | 550 $\mu$ H $\pm$ 10% | 100 kHz, 1 V                        |
| Primary-Side Effective Leakage ( $L_r$ ) | 2 6  | 110 $\mu$ H $\pm$ 10% | Short one of the Secondary Windings |

For more detailed information regarding the transformer, visit <http://www.santronics-usa.com/documents.html> or contact [sales@santronics-usa.com](mailto:sales@santronics-usa.com) or +1-408-734-1878 (Sunnyvale, California USA).

## Physical Dimensions



NOTES: UNLESS OTHERWISE SPECIFIED

- A. THIS PACKAGE DOES NOT COMPLY TO ANY CURRENT PACKAGING STANDARD.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS.
- D. DRAWING FILE NAME: MOD09ACREV2

**Figure 31. 9-Lead, SIP Module, Formed, Lead, 3.2 x 10.5 x 26 mm**

Package drawings are provided as a service to customers considering Fairchild components. Drawings may change in any manner without notice. Please note the revision and/or date on the drawing and contact a Fairchild Semiconductor representative to verify or obtain the most recent revision. Package specifications do not expand the terms of Fairchild's worldwide terms and conditions, specifically the warranty therein, which covers Fairchild products.

Always visit Fairchild Semiconductor's online packaging area for the most recent package drawings:  
<http://www.fairchildsemi.com/packaging/>


**TRADEMARKS**

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks.

|   |  |   |   |
|---|--|---|---|
| 2Cool™  | FPST™  |  | Sync-Lock™  |
| AccuPower™  | F-PFST™  | PowerTrench®  |  SYSTEM GENERAL® |
| AX-CAP®   | FRFET®   | PowerXS™  | TinyBoost™  |
| BitSiC™   | Global Power Resource™                         | Programmable Active Droop™  | TinyBuck™   |
| Build it Now™   | GreenBridge™                                   | QFET®   | TinyCalc™   |
| CorePLUS™   | Green FPS™                                     | QS™   | TinyLogic®  |
| CorePOWER™  | Green FPS™ e-Series™                           | Quiet Series™   | TINYOPTO™   |
| CROSSVOLT™  | Gmax™  | RapidConfigure™   | TinyPower™  |
| CTL™  | GTO™   |  | TinyPWM™  |
| Current Transfer Logic™   | IntelliMAX™                                    | Saving our world, 1mW/Wk/W at a time™   | TinyWire™   |
| DEUXPEED®   | ISOPLANAR™                                     | SignalWise™   | TranSiC™  |
| Dual Cool™  | Making Small Speakers Sound Louder and Better™ | SmartMax™   | TriFault Detect™  |
| EcoSPARK®   | MegaBuck™                                      | SMART START™  | TRUECURRENT®  |
| EfficientMax™   | MICROCOUPLER™                                  | Solutions for Your Success™   | μSerDes™  |
| ESBC™   | MicroFET™                                      | SPM®  |  SerDes™         |
|  | MicroPak™                                      | STEALTH™  | UHC®  |
| Fairchild®  | MicroPak2™                                     | SuperFET®   | Ultra FRFET™  |
| Fairchild Semiconductor®  | MillerDrive™                                   | SuperSOT™-3   | UniFET™   |
| FACT Quiet Series™  | MotionMax™                                     | SuperSOT™-6   | VXC™  |
| FACT®   | mWSaver™                                       | SuperSOT™-8   | VisualMax™  |
| FAST®   | OptoHi™  | SupreMOS®   | VoltagePlus™  |
| FastvCore™  | OPTOLOGIC®                                     | SyncFET™  | XS™   |
| FETBench™   | OPTOPLANAR®                                    |   |   |

\* Trademarks of System General Corporation, used under license by Fairchild Semiconductor.

**DISCLAIMER**

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN, NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

**LIFE SUPPORT POLICY**

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
2. A critical component in any component of a life support device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

**ANTI-COUNTERFEITING POLICY**

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, [www.fairchildsemi.com](http://www.fairchildsemi.com), under Sales Support.

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufacturers of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed applications, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handling and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address any warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

**PRODUCT STATUS DEFINITIONS**
**Definition of Terms**

| Datasheet Identification | Product Status        | Definition  |
|--------------------------|-----------------------|---|
| Advance Information      | Formative / In Design | Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.   |
| Preliminary              | First Production      | Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design. |
| No Identification Needed | Full Production       | Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.   |
| Obsolete                 | Not In Production     | Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.  |

Rev. I64

# AMEYA360

## Components Supply Platform

Authorized Distribution Brand :



Website :

Welcome to visit [www.ameya360.com](http://www.ameya360.com)

Contact Us :

➤ Address :

401 Building No.5, JiuGe Business Center, Lane 2301, Yishan Rd  
Minhang District, Shanghai , China

➤ Sales :

Direct +86 (21) 6401-6692

Email [amall@ameya360.com](mailto:amall@ameya360.com)

QQ 800077892

Skype [ameyasales1](#) [ameyasales2](#)

➤ Customer Service :

Email [service@ameya360.com](mailto:service@ameya360.com)

➤ Partnership :

Tel +86 (21) 64016692-8333

Email [mkt@ameya360.com](mailto:mkt@ameya360.com)